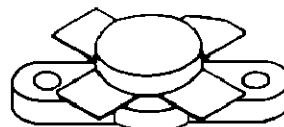


RF & MICROWAVE TRANSISTORS HF SSB APPLICATIONS

- OPTIMIZED FOR SSB
- 30 MHz
- 28 VOLTS
- IMD -30 dB
- COMMON EMITTER
- GOLD METALLIZATION
- $P_{OUT} = 130$ W PEP WITH 12 dB GAIN



.500 4LFL (M174)
epoxy sealed

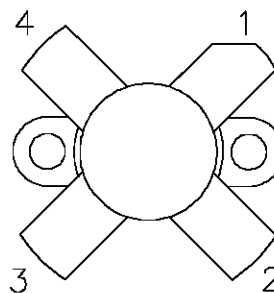
ORDER CODE
SD1729

BRANDING
TH416

DESCRIPTION

The SD1729 is a Class AB 28 V epitaxial silicon NPN planar transistor designed primarily for SSB communications. This device utilizes emitter ballasting to achieve extreme ruggedness under severe operating conditions.

PIN CONNECTION



- | | |
|--------------|------------|
| 1. Collector | 3. Base |
| 2. Emitter | 4. Emitter |

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}\text{C}$)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	70	V
V_{CEO}	Collector-Emitter Voltage	35	V
V_{EBO}	Emitter-Base Voltage	4.0	V
I_C	Device Current	12	A
P_{DISS}	Power Dissipation	175	W
T_J	Junction Temperature	+200	$^{\circ}\text{C}$
T_{STG}	Storage Temperature	- 65 to +150	$^{\circ}\text{C}$

THERMAL DATA

$R_{TH(j-c)}$	Junction-Case Thermal Resistance	1.0	$^{\circ}\text{C/W}$
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SD1729 (TH416)

ELECTRICAL SPECIFICATIONS ($T_{\text{case}} = 25^{\circ}\text{C}$)

STATIC

Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
BV_{CES}	$I_{\text{C}} = 50 \text{ mA}$	$V_{\text{BE}} = 0 \text{ V}$	70	—	—	V
BV_{CEO}	$I_{\text{C}} = 100 \text{ mA}$	$I_{\text{B}} = 0 \text{ mA}$	35	—	—	V
BV_{EBO}	$I_{\text{E}} = 20 \text{ mA}$	$I_{\text{C}} = 0 \text{ mA}$	4.0	—	—	V
I_{CES}	$V_{\text{CE}} = 35 \text{ V}$	$I_{\text{E}} = 0 \text{ mA}$	—	—	20	mA
h_{FE}	$V_{\text{CE}} = 5 \text{ V}$	$I_{\text{C}} = 7 \text{ A}$	18	—	50	—

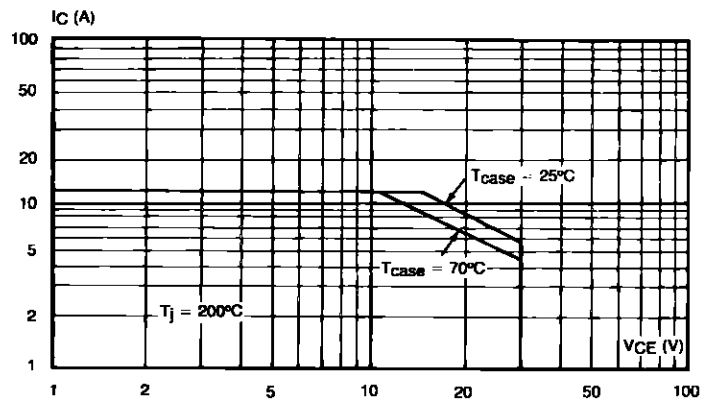
DYNAMIC

Symbol	Test Conditions			Value			Unit
				Min.	Typ.	Max.	
P_{OUT}	$f = 30 \text{ MHz}$	$V_{\text{CE}} = 28 \text{ V}$	$I_{\text{CQ}} = 150 \text{ mA}$	130	—	—	W
G_{P}	$P_{\text{OUT}} = 130 \text{ W PEP}$	$V_{\text{CE}} = 28 \text{ V}$	$I_{\text{CQ}} = 150 \text{ mA}$	12	—	—	dB
IMD^*	$P_{\text{OUT}} = 130 \text{ W PEP}$	$V_{\text{CE}} = 28 \text{ V}$	$I_{\text{CQ}} = 150 \text{ mA}$	—	—	-30	dBc
η_{C}	$P_{\text{OUT}} = 130 \text{ W PEP}$	$V_{\text{CE}} = 28 \text{ V}$	$I_{\text{CQ}} = 150 \text{ mA}$	37	—	—	%
C_{OB}	$f = 1 \text{ MHz}$	$V_{\text{CB}} = 28 \text{ V}$		—	220	—	pF

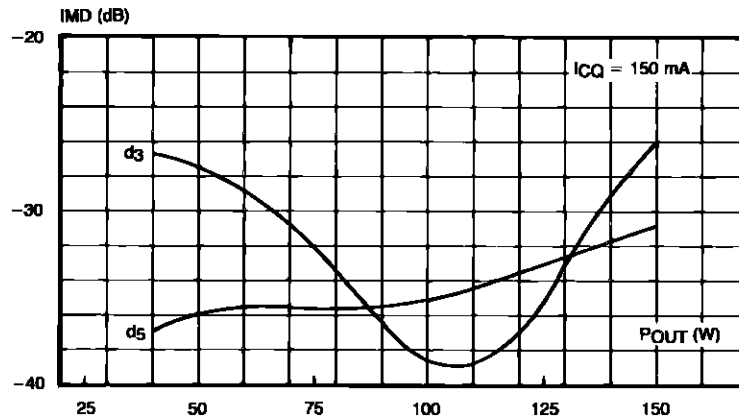
Note: * $f_1 = 30.00 \text{ MHz}$, $f_2 = 30.001 \text{ MHz}$

TYPICAL PERFORMANCE

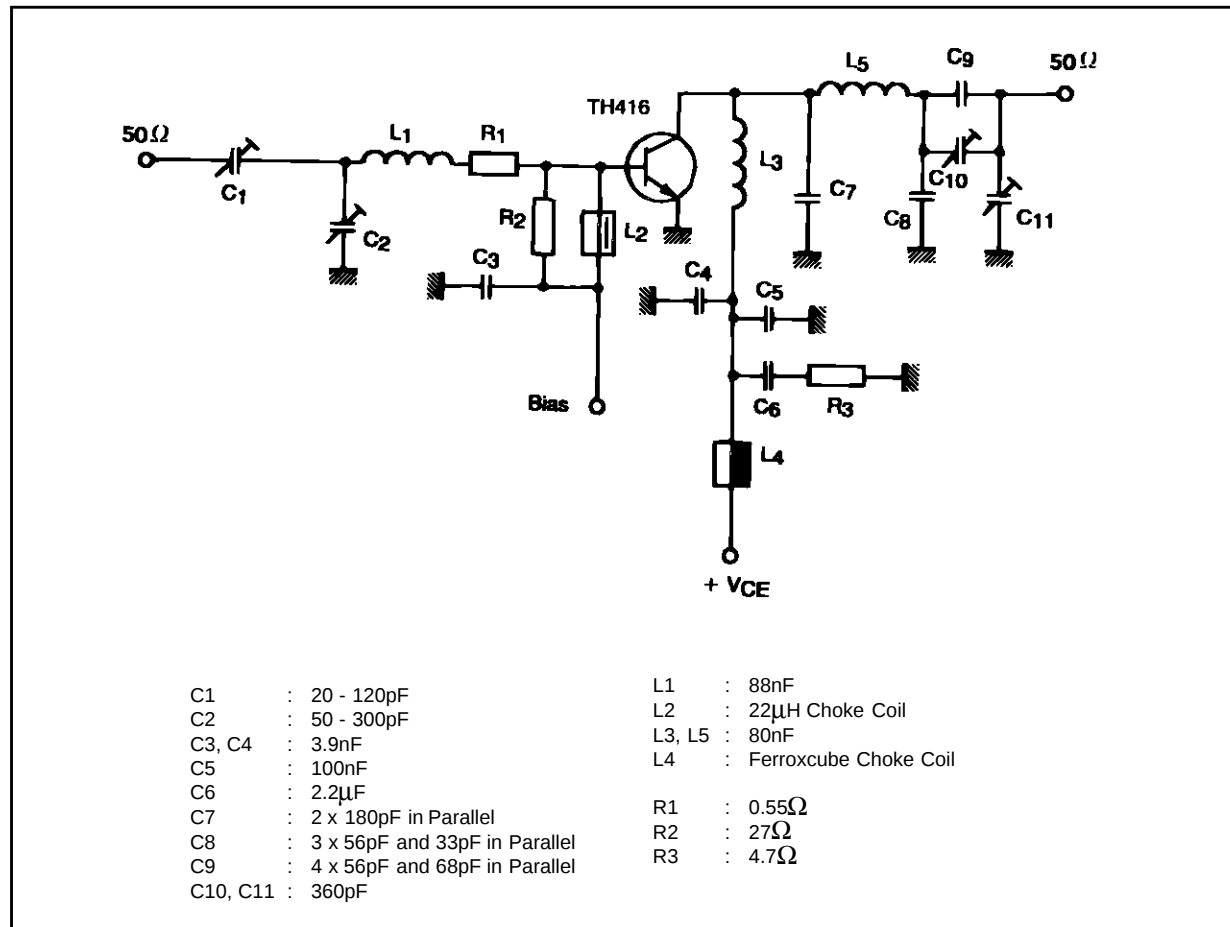
SAFE OPERATING AREA



TYPICAL PERFORMANCE (cont'd)

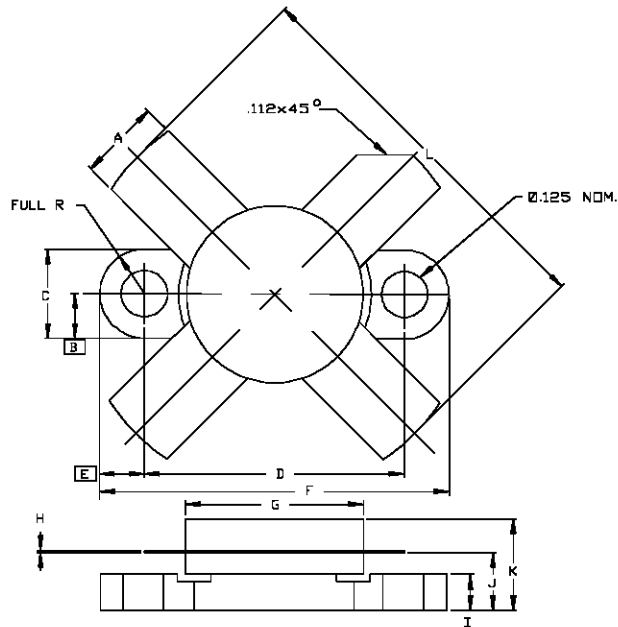
INTERMODULATION DISTORTION vs
POWER OUTPUT

TEST CIRCUIT



PACKAGE MECHANICAL DATA

Ref.: Dwg. No.12-0174



SGS-THOMSON MICROELECTRONICS			CONT'D		
	MINIMUM Inches/mm	MAXIMUM Inches/mm		MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.220/5,59	.230/5,84	K		.280/7,11
B	.125/3,18		L		1.050/26,67
C	.245/6,22	.255/6,48			
D	.720/18,28	.730/18,54			
E	.125/3,18				
F	.970/24,64	.980/24,89			
G	.495/12,57	.505/12,83			
H	.003/0,08	.007/0,18			
I	.090/2,29	.110/2,79			
J	.160/4,06	.175/4,45			

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